



NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

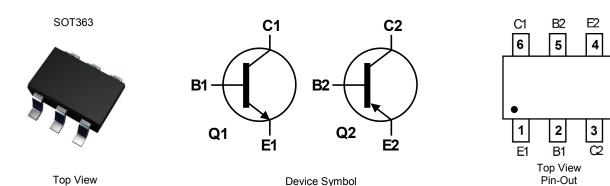
Features

- Epitaxial Planar Die Construction
- Complementary Pair
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMDT5451Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



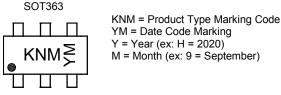
Ordering Information (Note 4)

| Part Number | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|-------------|------------|---------|--------------------|-----------------|-------------------|
| MMDT5451Q-7 | AEC-Q101 | KNM | 7 | 8 | 3,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Date Code Key

| Year | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | I | J | K | L | М | N | 0 | Р | R | S | Т | U |
| | | | | | | | | A | 0 | 0-4 | Nav | Dan |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | | | | | | | | | | | | |

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Absolute Maximum Ratings – NPN (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 180 | V |
| Collector-Emitter Voltage | V _{CEO} | 160 | V |
| Emitter-Base Voltage | V _{EBO} | 6 | V |
| Continuous Collector Current | Ic | 200 | mA |

Absolute Maximum Ratings - PNP (@ TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | -160 | V |
| Collector-Emitter Voltage | V _{CEO} | -150 | V |
| Emitter-Base Voltage | V_{EBO} | -6 | V |
| Continuous Collector Current | Ic | -200 | mA |

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit | |
|---|-----------------------------------|----------------|-------|------|--|
| Power Dissipation | (Note 5) | Б | 200 | mW | |
| Power Dissipation | (Note 6, 7) | P _D | 320 | | |
| Thermal Resistance, Junction to Ambient | (Note 5) | Ь | 625 | | |
| Thermal Resistance, Junction to Ambient | (Note 6, 7) | $R_{	heta JA}$ | 390 | °C/W | |
| Thermal Resistance, Junction to Case | $R_{	heta JC}$ | 140 | | | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C | | |

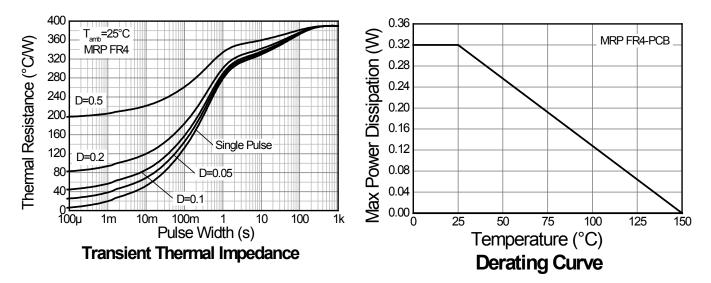
Notes:

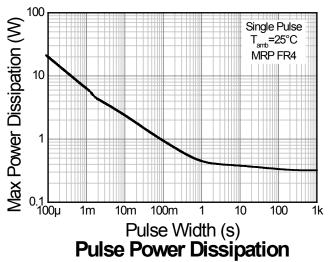
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^{5.} For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device uses 2oz copper.
7. Maximum combined dissipation.
8. Thermal resistance from junction to the top of package.



Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)







Electrical Characteristics – NPN (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | | |
|--|----------------------|-----|-----|------|------|---|--|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Collector-Base Breakdown Voltage | BV _{CBO} | 180 | _ | _ | V | $I_C = 100\mu A, I_E = 0$ | | |
| Collector-Emitter Breakdown Voltage (Note 9) | BV _{CEO} | 160 | _ | _ | V | $I_C = 1mA, I_B = 0$ | | |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 6 | _ | _ | V | $I_E = 10\mu A, I_C = 0$ | | |
| Collector-Base Cutoff Current | _ | _ | _ | 50 | nA | V _{CB} = 120V, I _E = 0 | | |
| Collector-Base Cuton Current | I _{CBO} | _ | _ | 50 | μΑ | V _{CB} = 120V, I _E = 0, T _A = +100°C | | |
| Base-Emitter Cutoff Current | I _{EBO} | _ | _ | 50 | nA | V _{EB} = 4V, I _C = 0 | | |
| ON CHARACTERISTICS (Note 9) | | | | | | | | |
| | | 80 | | _ | | I _C = 1.0mA, V _{CE} = 5.0V | | |
| DC Current Gain | h _{FE} | 80 | _ | 250 | _ | I _C = 10mA, V _{CE} = 5.0V | | |
| | | 30 | | _ | | $I_C = 50mA, V_{CE} = 5.0V$ | | |
| Collector Emitter Seturation Voltage | V | _ | | 0.15 | V | I _C = 10mA, I _B = 1.0mA | | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | | _ | 0.20 | V | $I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$ | | |
| Dage Emitter Ceturation Voltage | V/ | | | 4.0 | V | I _C = 10mA, I _B = 1.0mA | | |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | _ | _ | 1.0 | | I _C = 50mA, I _B = 5.0mA | | |
| SMALL SIGNAL CHARACTERISTICS | | | | | | | | |
| Output Capacitance | C _{obo} | | | 6.0 | pF | V _{CB} = 10V, f = 1.0MHz, I _E = 0 | | |
| Small Signal Current Gain | h _{fe} | 50 | | 250 | _ | I _C = 1mA, V _{CE} = 10V, f = 1.0MHz | | |
| Current Gain-Bandwidth Product | f⊤ | 100 | _ | 300 | MHz | I _C = 10mA, V _{CE} = 10V, f = 100MHz | | |

Electrical Characteristics - PNP (@ TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | | |
|--|----------------------|------|-----|-------|------|--|--|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Collector-Base Breakdown Voltage | BV _{CBO} | -160 | _ | _ | V | $I_C = -100\mu A, I_E = 0$ | | |
| Collector-Emitter Breakdown Voltage (Note 9) | BV_{CEO} | -150 | _ | _ | V | $I_{C} = -1 \text{mA}, I_{B} = 0$ | | |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -6 | _ | _ | V | $I_E = -10\mu A, I_C = 0$ | | |
| Collector-Base Cutoff Current | - | | _ | -50 | nA | V _{CB} = -120V, I _E = 0 | | |
| Collector-base Cuton Current | I _{CBO} | | _ | -50 | μA | V _{CB} = -120V, I _E = 0, T _A = +100°C | | |
| Base-Emitter Cutoff Current | I _{EBO} | _ | _ | -50 | nA | V _{EB} = -4V, I _C = 0 | | |
| ON CHARACTERISTICS (Note 9) | | | | | | | | |
| | | 50 | | _ | | I _C = -1.0mA, V _{CE} = -5.0V | | |
| DC Current Gain | h _{FE} | 60 | _ | 240 | _ | $I_C = -10$ mA, $V_{CE} = -5.0$ V | | |
| | | 50 | | _ | | I _C = -50mA, V _{CE} = -5.0V | | |
| Collector Emitter Saturation Voltage | V | | | -0.20 | V | $I_C = -10mA$, $I_B = -1.0mA$ | | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | _ | | -0.50 | ٧ | $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$ | | |
| Base-Emitter Saturation Voltage | V | | | -1.0 | V | $I_C = -10mA$, $I_B = -1.0mA$ | | |
| Base-Emiller Saturation Voltage | V _{BE(sat)} | _ | _ | -1.0 | V | I _C = -50mA, I _B = -5.0mA | | |
| SMALL SIGNAL CHARACTERISTICS | | | | | | | | |
| Output Capacitance | C_{obo} | | | 6.0 | pF | $V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$ | | |
| Small Signal Current Gain | h _{fe} | 40 | | 260 | | $I_C = -1 \text{mA}, V_{CE} = -10 \text{V}, f = 1.0 \text{MHz}$ | | |
| Current Gain-Bandwidth Product | f _T | 100 | _ | 300 | MHz | I _C = -10mA, V _{CE} = -10V, f = 100MHz | | |

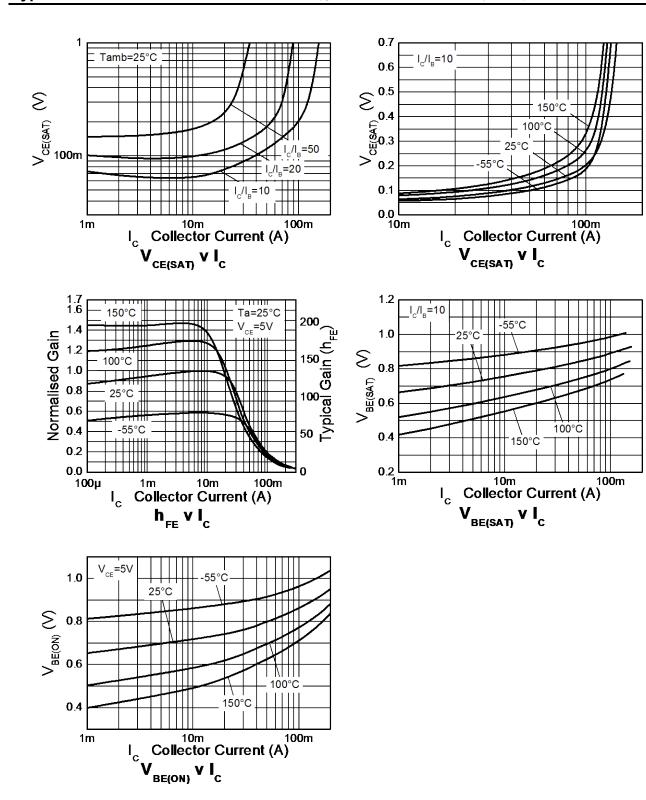
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

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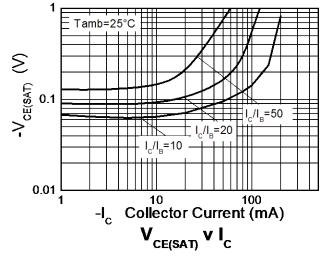


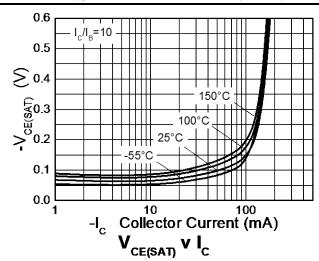
Typical Electrical Characteristics – NPN (@ T_A = +25°C, unless otherwise specified.)

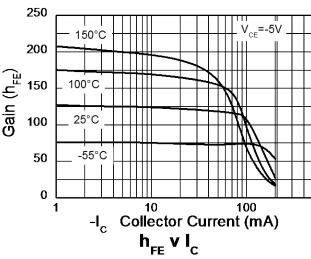


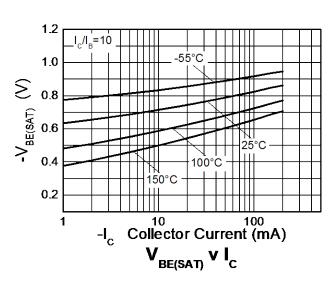


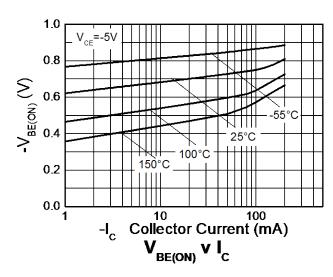
Typical Electrical Characteristics - PNP 5401 Section (@ TA = +25°C, unless otherwise specified.)









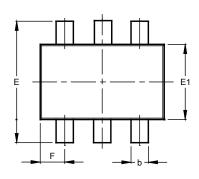


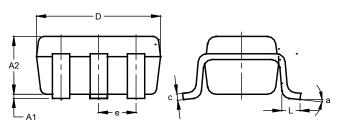


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



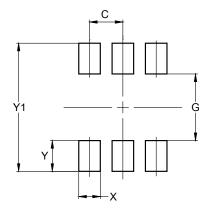


| SOT363 | | | | | | |
|--------|-------|---------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| A1 | 0.00 | 0.10 | 0.05 | | | |
| A2 | 0.90 | 1.00 | 1.00 | | | |
| b | 0.10 | 0.30 | 0.25 | | | |
| С | 0.10 | 0.22 | 0.11 | | | |
| D | 1.80 | 2.20 | 2.15 | | | |
| E | 2.00 | 2.20 | 2.10 | | | |
| E1 | 1.15 | 1.35 | 1.30 | | | |
| е | C |).650 B | SC | | | |
| F | 0.40 | 0.45 | 0.425 | | | |
| L | 0.25 | 0.40 | 0.30 | | | |
| а | 0° | 8° | | | | |
| All | Dimen | sions | in mm | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



| Dimensions | Value |
|---------------|---------|
| Dillielisions | (in mm) |
| С | 0.650 |
| G | 1.300 |
| Х | 0.420 |
| Υ | 0.600 |
| Y1 | 2.500 |

September 2021

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